



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Milan Kokta, et al.

Title: SPINEL ARTICLES AND METHODS FOR FORMING SAME

Application No.: 10/669,135

Filed: September 23, 2003

Examiner: Felisa Carla Hiteshew

Group Art Unit: 1765

Atty. Docket No.: 1035-BI4307

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Alexandria, VA 22313-1450

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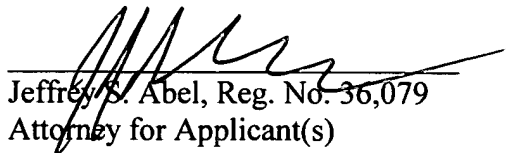
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Date 1/25/05

Respectfully submitted,


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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/669,135
		Filing Date	September 23, 2003
		First Named Inventor	Milan R. Kokta
		Art Unit	1765
		Examiner Name	Felisa Carla Hiteshew
Sheet 2	of 3	Attorney Docket Number	1035-BI4307

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	BA	Efimov, A.N., et al., "Onan Unusual Azimuthal Orientation Relationship in the System Gallium Nitride Layer on Spinel Substrate", CRYSTALLOGRAPHY REPORTS, 45(2): 312-317 (2000).	
	BB	Sun C.J., et al., "Mg-doped green light emitting diodes over cubic (1 1 1) MgAl ₂ O ₄ substrate", APP. PHYS. LETT. 72(19): 2361-2363 (1998).	
	BC	Efimov, A.N., et al., "Symmetry constraints and epitaxial growth on non-isomorphic substrate", THIN SOLID FILMS 260: 111-117 (1995).	
	BD	George, T., et al., "Novel symmetry in the growth of gallium nitride on magnesium aluminate substrates", APPL. PHYS. LETT. 68(3): 337-339 (1996).	
	BE	Sun C.J., et al., "Deposition of high quality wurtzite GaN films over cubic (1 1 1) MgAl ₂ O ₄ substrates using low pressure and metalorganic chemical vapor deposition," APPL. PHYS. LETT. 68(8): 1129-1131 (1996).	
	BF	Nakamura, S., et al., "Characteristics of InGaN multi-quantum-well-structure laser diodes," APPL. PHYS. LETT. 68(23): 3269-3271 (1996).	
	BG	Khan, M.A., et al., "Cleaved cavity optically pumped InGaN-GaN laser grown on spinel substrates," APPL. PHYS. LETT. 69(16): 2418-2420 (1996).	
	BH	Tempel, A., et al., "Nachweis von Stapelfehlern in GaN-Epitaxieschichten mittels Elektronenbeugung," KRISTALL UND TECHNIK 10(7): 741-746 (1975).	
	BI	Tempel, A., et al., "Zur Epitaxie von Galliumnitride auf nichtstoechiometrischem Spinell im System GaC ₁ /NH ₃ /He," KRISTALL UND TECHNIK 10(7): 747-758 (1975)	
	BJ	K.V. Yumashev, "Saturable absorber Co ²⁺ : MgAl ₂ O ₃ crystal for Q switching of 1.34-um Nd ³⁺ : YAlO ₃ and 1.54-um Er ³⁺ : glass lasers," APPLIED OPTICS 38(30): 6343-6346 (1999).	

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	CA	Camargo, M.B., et al., "Co2+ Y3Sc2Ga3O12 (YSGG) Passive Q-Switch for Infared Erbium Lasers," submitted to LEOS in 1994.	
	CB	Mikhailov, V.P., et al., "Passive Q-switch performance at 1.3u (1.5u) and nonlinear spectroscopy of Co2+: MgAl2O4 and Co2+: LaMgAl11O9 crystals," OSA TOPS VOL. 26 Advanced Solid-State Lasers, pp. 317-324 (1999).	
	CC	Stulz, R.D., et al., "Divalent Uranium and Cobalt Saturable Absorber Q-Switches at 1.5um," OSA Proceedings on Advanced Solid-State Lasers, 24:460-464 (1995).	
	CD	Birnbaum, M., et al., "Co2+: ZnSe Saturable Absorber Q-Switch for the 1.54 Um Er3+: Yb3+: Glass Laser," OSA TOPS Vol. 10 Advanced Solid State Lasers, pp. 148-151 (1997).	
	CE	Machida, H., et al., "difficulties encountered during the Czochralski growth of TiO2 single crystals," JOURNAL OF CRYSTAL GROWTH, 112: 835-837 (1997).	
	CF	Camargo, M.B., et al., "Broad-band 1.54 um Saturable Absorber Q-switch with Co2+, " submitted to ASSL in 1995.	
	CG	Yumashev, K.V., et al., "Nonlinear spectroscopy and passive Q-switching operation of a Co2+: LaMgAl11O19 crystal," J. OPT. SOC. AM. B., 16(12): 2189-2194 (1999).	
	CH		
	CI		
	CJ		

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